



# Cross-die timing methodology for Next-Gen Chiplet SoCs

A shift-left solution for cross-foundry 3DIC-STA Signoff

**DEEPON SAHA**

ADVANCED MICRO DEVICES

Co-Authors (AMD)

ANIMESH SHARMA

ANIMESH JAIN



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# AGENDA

- MOTIVATION
- CHALLENGES
- MAIN IDEA
- IMPLEMENTATION
- PERFORMANCE
- SILICON CORRELATION
- FUTURE EFFORTS
- CONCLUSION



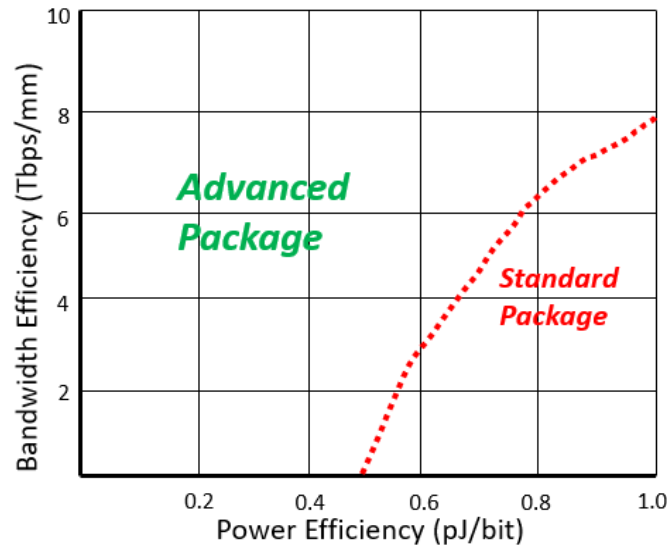
# MOTIVATION

To keep the Moore's law alive, Chiplet with advance packaging are increasingly becoming the mainstream design choice. **CHIPLETS** are small modular chips packaged together, which if required can collectively work as a single unit.

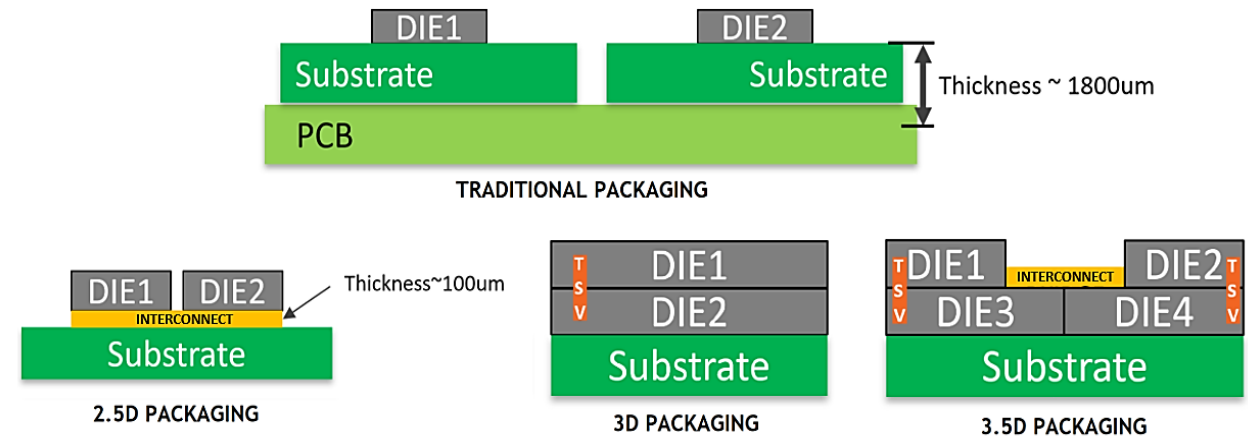


A generic Chiplet configuration includes multiple dies placed over a package substrate which provides connections to PCB, while an Interposer enables connections between dies and substrate.

# MOTIVATION (CONTD.)



**BANDWIDTH vs POWER EFFICIENCY TRENDS**

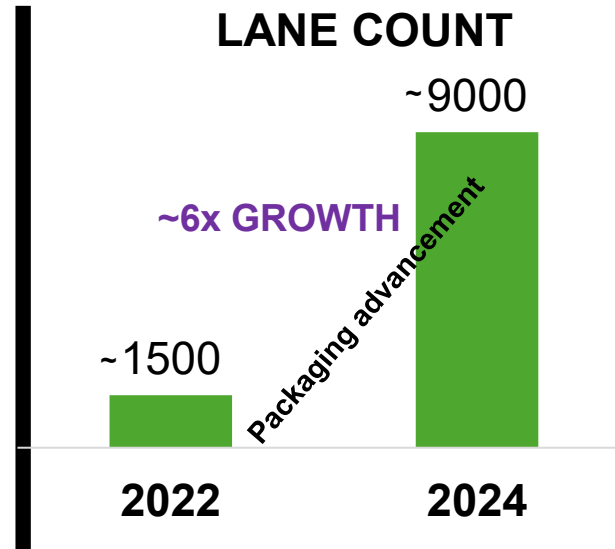
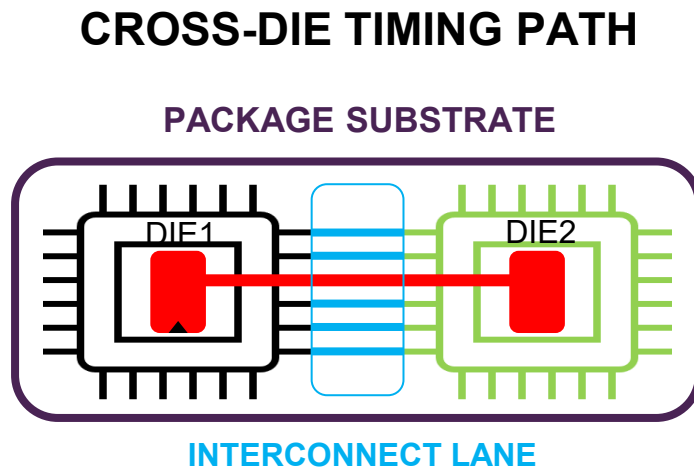


**PACKAGING OPTIONS**

- ▲ Advanced packaging techniques categorized as 2.5D, 3D & 3.5D Integration allows for higher die density while standardization of cross-die short reach PHY enables flexibility & interoperability to mix & match dies from different tech nodes or foundries altogether.
- ▲ Due to shorter interconnect distance, the dies can communicate using a simpler source-synchronous/clock-forwarding PHY architecture.

Cross-die/cross-tech timing closure scenario as the new ask of the hour.

# CHALLENGES



- While link budgeting in terms of Signal Integrity/Power Supply Jitter analysis is still an integral part of sign-off; a low power PHY operating at low speed via short reach channel opens the possibility of cross-die STA + spice based margining methodology to become a substitute in future.

- The prime challenge to support the package level cross-die path timing becomes difficult as the lane count keeps increasing, thus paving more and more challenges to sign-off in single timing environment:

1. Formation of unit package level design netlist combining all dies within a single package.
2. Full-chip STA environment is complicated and has high run-time penalty; scaling to package level will not yield any return on investment.
3. All future cross-die path will be multi-tech-node type designs, which requires significant effort to setup flows and methodology.

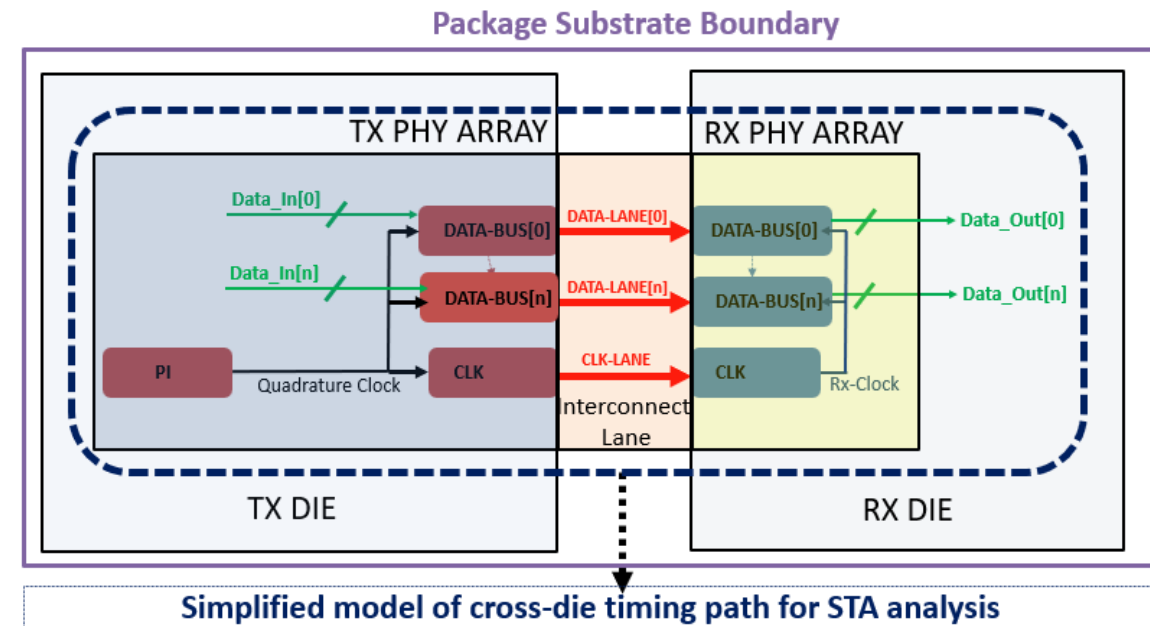
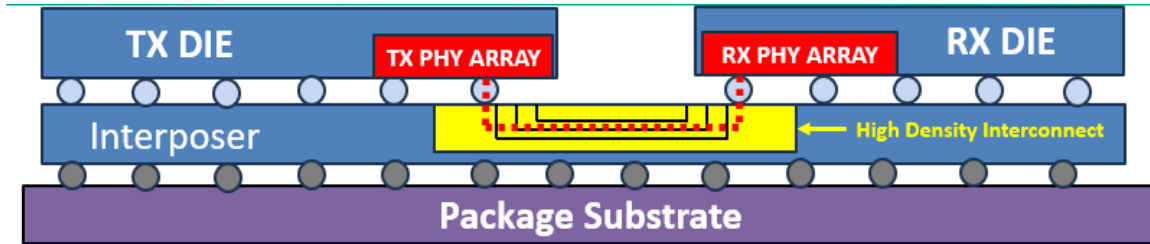
# MAIN IDEA

- ▲ To address the above challenges, a novel “3DIC Cross-Die Static Timing Analysis & methodology” (3DIC-STA) with following elements is proposed :

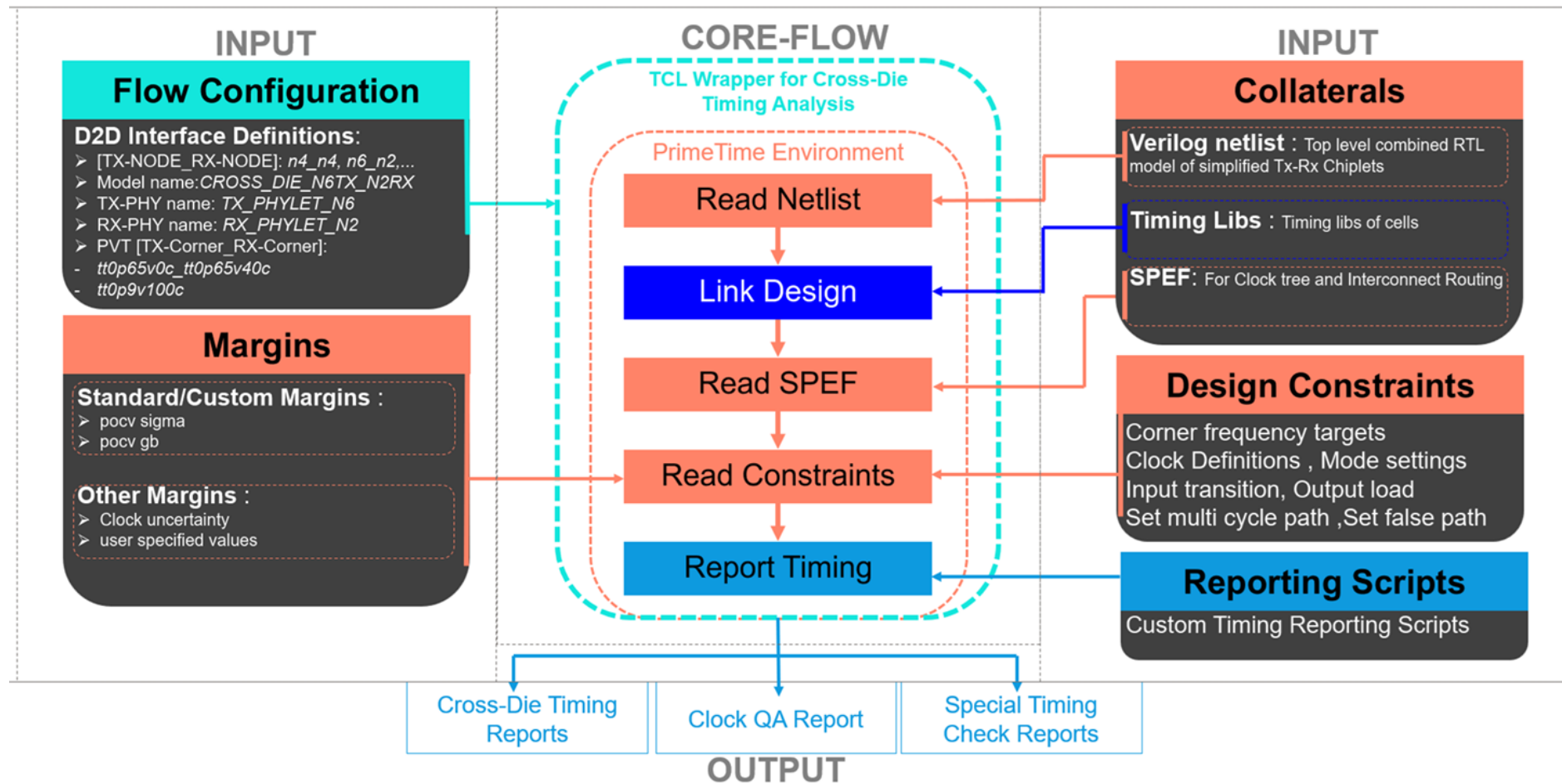
**A. Simplified model of cross-die path:** Using reduced Transmitter (Tx) and Receiver (Rx) PHY logic placed at the chip boundary.

**A. Custom PrimeTime based cross-die flow:** We use the simplified model of cross-die timing paths to setup a package-level timing environment using a custom-built flow.

**A. SPICE based precise STA signoff margining:** Traditional STA pessimistic margining at full-chip level is not beneficial in terms of Power-Performance-Area (PPA). SPICE simulations models the variation and other non-linearity, which is then utilized for accurate margining in STA.



# IMPLEMENTATION



A Generic, Scalable, Faster solution which required silicon data for correlation & sign-off confidence.

# PERFORMANCE

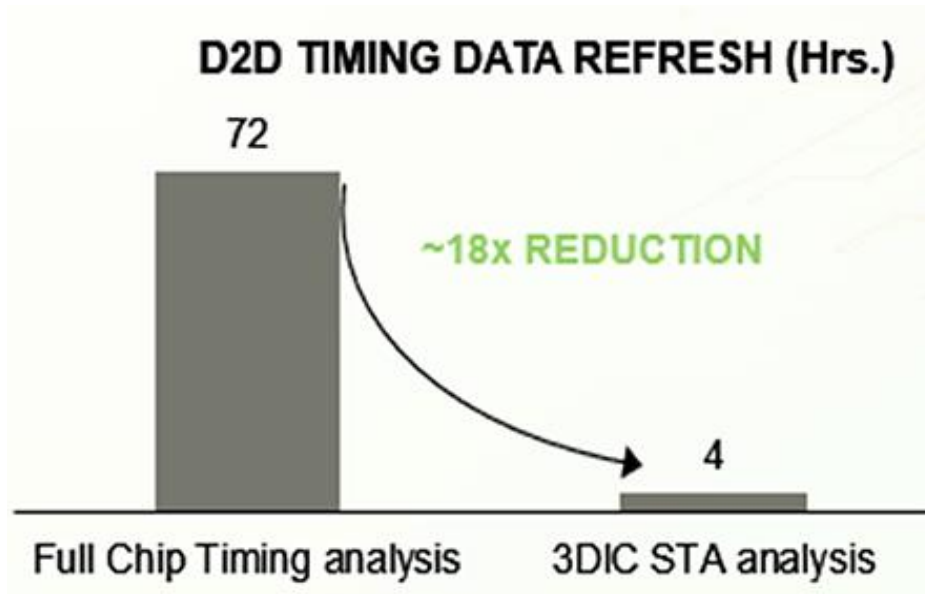
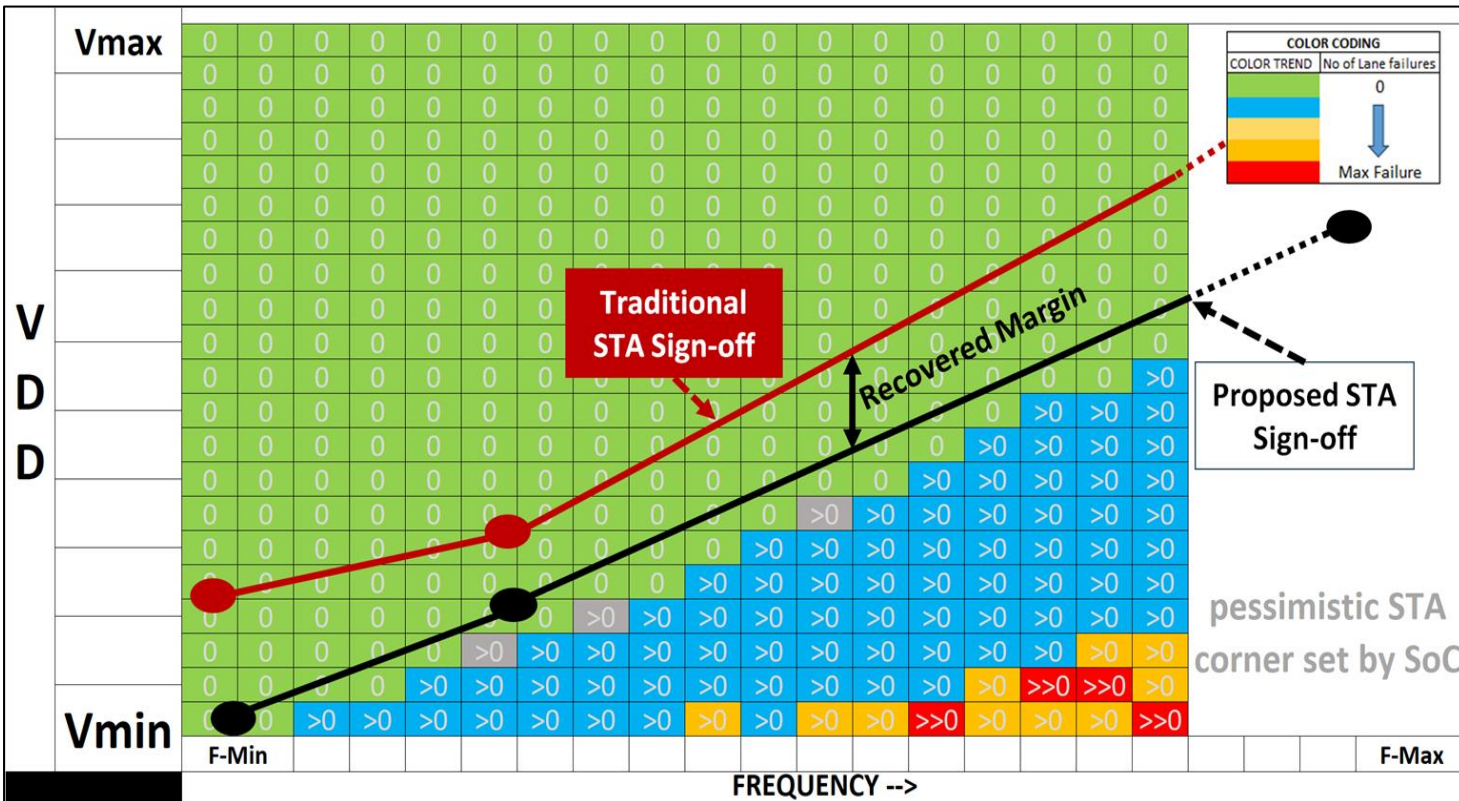


Figure describes the approximate run-time improvement as compared to an equivalent best-case analysis based on full-chip timing with respect to worst-case runtime with proposed 3DIC-STA solution – as is evident from the diagram we see a significant runtime improvement of approximately 18x (thanks to the simplified model explained in slide #6).



# SILICON CORRELATION



Success of the silicon on a specific voltage-frequency (VF) is defined by number of lane failures. The data has been color coded for ease of visualization. The green area representing VF combination with **zero** lane failures, while the blue-orange-red area represents higher lane failures.

The proposed 3DIC-STA flow was also successful in recovering hidden margins in the design.

SHMOO PLOT DESCRIBING SILICON CORRELATION WITH 3DIC-STA BASED SIGNOFF



All lane failures are observed beyond the STA target range, thereby establishing accuracy of the 3DIC STA Solution. Further, the difference between RED & BLACK line shows the STA margins that were recovered leading to better performance per watt.

# FUTURE WORK

- ▲ There's a trend of consistent increase in die-to-die lane count, which will further accelerate with higher stacking density. It will result in significant increase in die-to-die source-synchronous paths, which is a perfect application for the proposed 3DIC-STA Solution for package level co-design.
- ▲ The proposed methodology can be further improved for future package-level co-design requirements with following areas of improvement:

## AUTOMATED CIRCUIT REDUCTION

CREATE SIMPLIFIED MODEL  
OF CROSS-DIE PATHS  
FOR ALL LANES.

## AUTOMATED CORRELATION WITH FULL CHIP TIMING

TO ALLOW EFFICIENT  
CORRELATION WITH FULL  
CHIP TIMING.

## PACKAGE LEVEL CO- DESIGN ENHANCEMENT

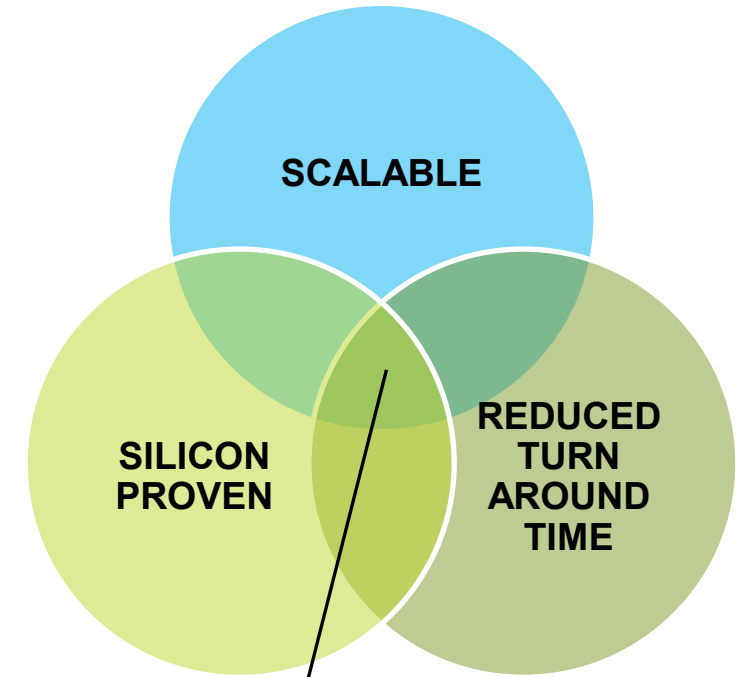
EXTEND TO OTHER SIGNOFF  
AREAS SUCH AS THERMAL,  
STRESS & RELIABILITY.

## TIMING BUDGETING BASED SIGN-OFF

AUTOMATED CROSS-DIE  
BUDGETING BASED SIGNOFF;  
ENABLING BOARD LIKE PLUG-  
AND-PLAY CONVENIENCE.

# CONCLUSION

- ▲ Following are the novelty elements associated with cross-die STA solution:
  - ▲ Industry leading package level die-to-die STA flow supporting signoff across processes, technology nodes and foundries.
  - ▲ Scalable to in-package die-to-die interfaces of various lane/array sizes.
  - ▲ Silicon proven Signoff accuracy aided by SPICE based precise margining, leading to extra margin recovery.
  - ▲ Faster turn-around time compared to a monolithic full-chip STA run due to efficient reduction of database.



Enabling shift-left capability to pre-fetch full-chip issues

# Q&A

